FM30H120G/M

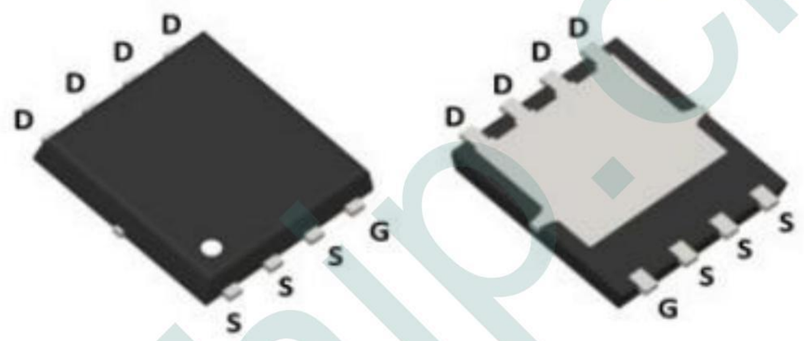
N-Channel Trench Power MOSFET

- 30V,120A
- RDS(ON)=2.7mΩ (Typ.) @ VGS =10V
- RDS(ON)=5.0mΩ (Typ.) @ VGS =4.5V

Application

- Load Switch
- PWM Application

Package



PDFN-8（5*6）

Absolute Maximum Ratings (TJ = 25°C unless otherwise noted)

Symbol	Parameter	Units	Maximum
V_{DS}	Drain-Source Voltage	V	30
V_{GS}	Gate-to-Source Voltage	V	±20
I_D @ T_C = 25°C	Continuous Drain Current	A	120
I_D @ T_C = 100°C	Continuous Drain Current	A	32
I_{DM}	Pulsed Drain Current	A	320
P_D	Power Dissipation	W	48
	Derating Factor	W/°C	0.26
E_{AS}	Single pulse avalanche energy○4	mJ	324
T_J	Operating Junction Temperature Range	°C	-55 to + 150
T_{STG}	Storage Temperature Range	°C	-55 to + 150

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